



# 安徽富信半导体科技有限公司

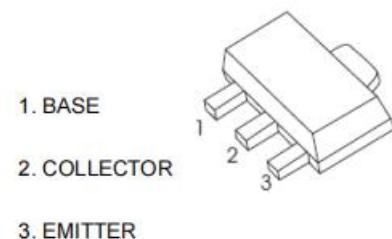
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

2SD1119

## SOT-89 Bipolar Transistor 双极型三极管

### ■ Features 特点

NPN Low Saturation Voltage 低饱和压降



### ■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage 集电极发射极电压	V <sub>CEO</sub>	25	V
Emitter-Base Voltage 发射极基极电压	V <sub>EBO</sub>	7	V
Collector Current 集电极电流	I <sub>C</sub>	3000	mA
Power dissipation 耗散功率	P <sub>C</sub> (T <sub>a</sub> =25°C)	500	mW
Thermal Resistance Junction-Ambient 热阻	R <sub>θJA</sub>	250	°C/W
Junction and Storage Temperature 结温和储藏温度	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

### ■ Device Marking 产品打标

H <sub>FE</sub>	230-380(Q)	340-600(R)
Mark	TQ	TR



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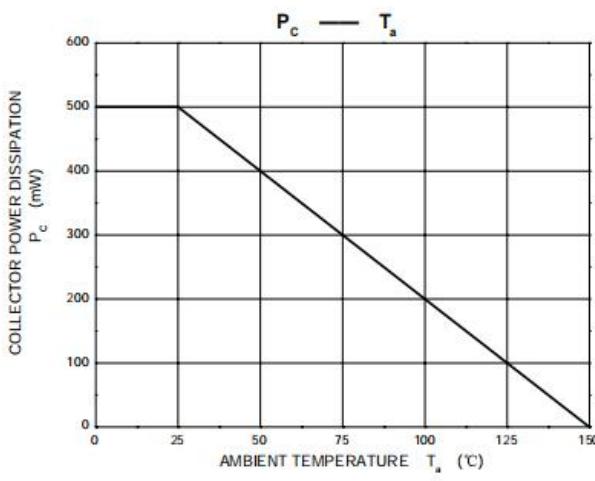
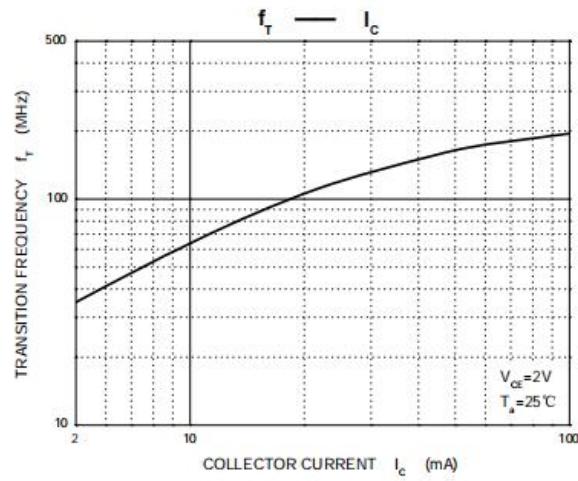
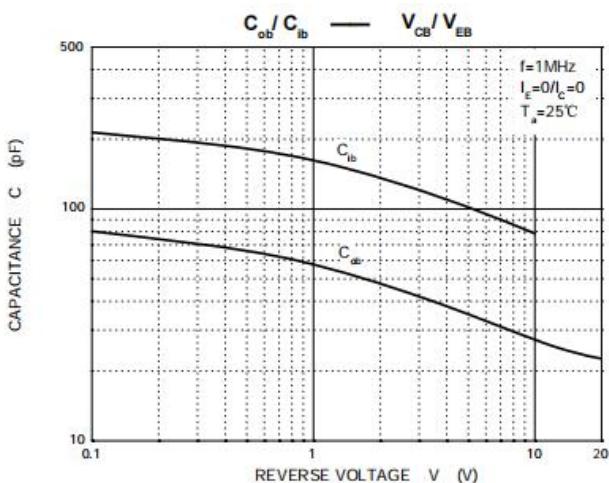
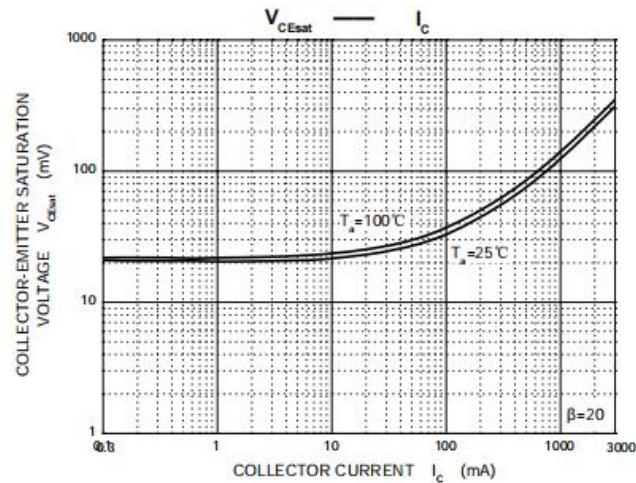
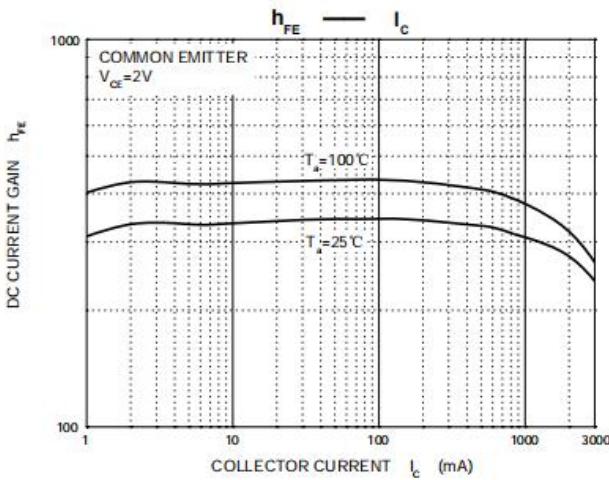
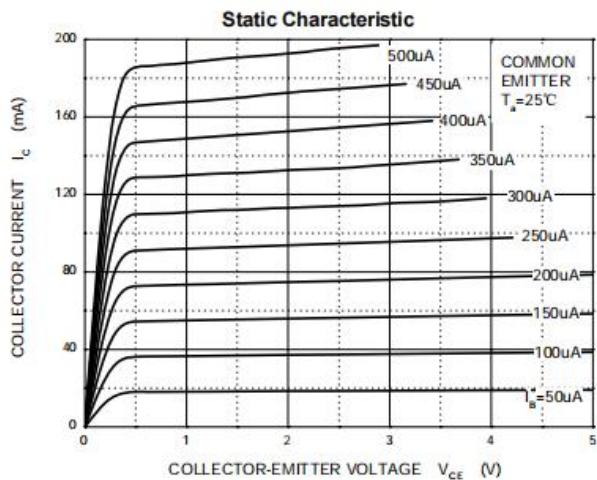
2SD1119

## ■ Electrical Characteristics 电特性

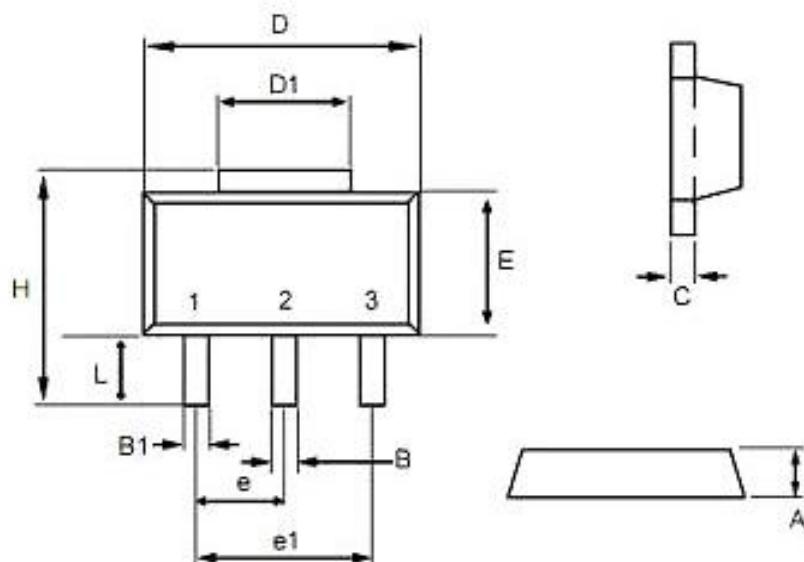
( $T_A=25^\circ\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压( $I_C=100\mu\text{A}$ , $I_E=0$ )	$\text{BV}_{\text{CBO}}$	40	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压( $I_C=1\text{mA}$ , $I_B=0$ )	$\text{BV}_{\text{CEO}}$	25	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压( $I_E=10\mu\text{A}$ , $I_C=0$ )	$\text{BV}_{\text{EBO}}$	7	—	—	V
Collector-Base Leakage Current 集电极基极漏电流( $V_{\text{CB}}=10\text{V}$ , $I_E=0$ )	$I_{\text{CBO}}$	—	—	0.1	$\mu\text{A}$
Collector-Base Leakage Current 集电极基极漏电流( $V_{\text{EB}}=6\text{V}$ , $I_E=0$ )	$I_{\text{EBO}}$	—	—	0.1	$\mu\text{A}$
DC Current Gain( $V_{\text{CE}}=2\text{V}$ , $I_C=500\text{mA}$ ) 直流电流增益( $V_{\text{CE}}=2\text{V}$ , $I_C=1000\text{mA}$ )	$H_{\text{FE}}$	230 150	—	600	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降( $I_C=3\text{A}$ , $I_B=100\text{mA}$ )	$V_{\text{CE}(\text{sat})}$	—	—	1	V
Output Capacitance 输出电容( $V_{\text{CB}}=20\text{V}$ , $I_E=0$ , $f=1\text{MHz}$ )	$C_{\text{ob}}$	—	50	—	pF
Transition Frequency 特征频率( $V_{\text{CE}}=6\text{V}$ , $I_C=50\text{mA}$ )	$f_T$	—	150	—	MHz

## ■ Typical Characteristic Curve 典型特性曲线



## ■ Dimension 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20